

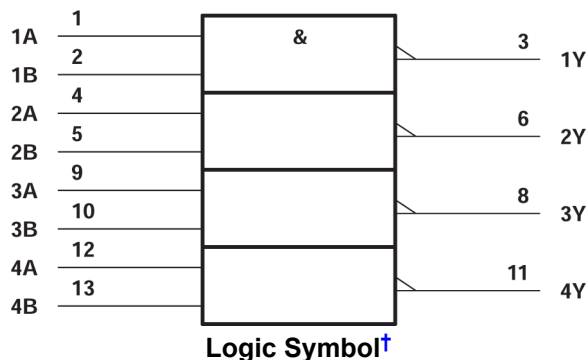
# SN74AHCT00Q-Q1 Automotive Quadruple 2-Input Positive-NAND Gates

## 1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C4B
- Available in [wetttable flank](#) QFN (WBQA) package
- Operating range of 4.5V to 5.5V
- Low power consumption, 10µA maximum I<sub>CC</sub>
- ±8mA output drive at 5V
- Inputs are TTL-voltage compatible
- Latch-up performance exceeds 250mA per JESD 17

## 2 Applications

- [Enable or disable a digital signal](#)
- [Controlling an indicator LED](#)
- [Translation between communication modules and system controllers](#)



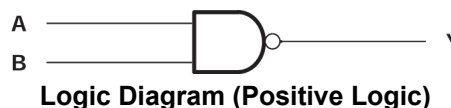
## 3 Description

The SN74AHCT00Q-Q1 performs the Boolean function  $Y = \overline{A \cdot B}$  or  $Y = \overline{A} + \overline{B}$  in positive logic.

### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>	BODY SIZE <sup>(3)</sup>
SN74AHCT00Q-Q1	D (SOIC, 14)	8.65mm × 6mm	8.65mm × 3.90mm
	PW (TSSOP, 14)	5.00mm × 6.4mm	5.00mm × 4.40mm
	BQA (WQFN, 14)	3.00mm × 2.50mm	3.00mm × 2.50mm

- (1) For more information, see [Section 11](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.



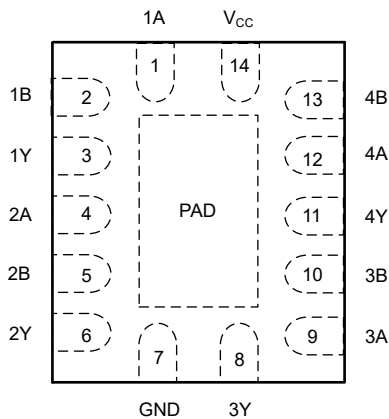
† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



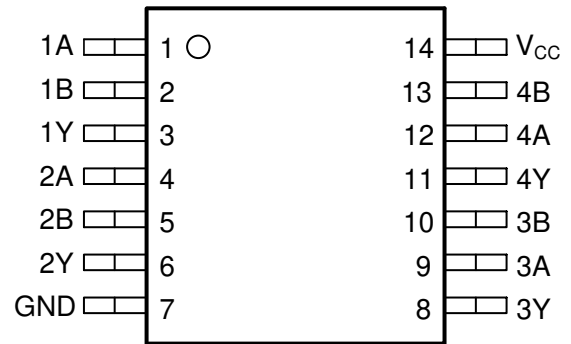
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## 4 Pin Configuration and Functions



**Figure 4-1. BQA Package, 14-Pin WQFN (Top View)**



**Figure 4-2. D or PW Package, 14-Pin SOIC or TSSOP (Top View)**

**Table 4-1. Pin Functions**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
1A	1	I	Channel 1, Input A
1B	2	I	Channel 1, Input B
1Y	3	O	Channel 1, Output Y
2A	4	I	Channel 2, Input A
2B	5	I	Channel 2, Input B
2Y	6	O	Channel 2, Output Y
GND	7	—	Ground
3Y	8	O	Channel 3, Output Y
3A	9	I	Channel 3, Input A
3B	10	I	Channel 3, Input B
4Y	11	O	Channel 4, Output Y
4A	12	I	Channel 4, Input A
4B	13	I	Channel 4, Input B
V <sub>CC</sub>	14	—	Positive Supply
Thermal Pad <sup>(2)</sup>		—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

(1) I = input, O = output, I/O = input or output, G = ground, P = power.

(2) BQA package only

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	VALUE
V <sub>CC</sub>	Supply voltage range	-0.5	7	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>	-0.5	7	V
V <sub>O</sub>	Output voltage range <sup>(2)</sup>	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub> (V <sub>I</sub> < 0)	Input clamp current		-20	mA
I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )	Output clamp current		±20	mA
I <sub>O</sub> (V <sub>O</sub> = 0 to V <sub>CC</sub> )	Continuous output current		±25	mA
	Continuous current through V <sub>CC</sub> or GND		±50	mA
T <sub>stg</sub>	Storage temperature range	-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 5.2 Recommended Operating Conditions

(over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>)

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	4.5	5.5	V
V <sub>IH</sub>	High-level input voltage	2		V
V <sub>IL</sub>	Low-level input voltage		0.8	V
V <sub>I</sub>	Input voltage	0	5.5	V
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>	V
I <sub>OH</sub>	High-level output current		-8	mA
I <sub>OL</sub>	Low-level output current		8	mA
Δt/Δv	Input transition rise or fall rate		20	ns/V
T <sub>A</sub>	Operating free-air temperature	-40	125	°C

- (1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, [Implications of Slow or Floating CMOS Inputs](#).

### 5.3 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74AHCT00Q-Q1			UNIT
		D (SOIC)	PW (TSSOP)	BQA (WQFN)	
		14 PINS	14 PINS	14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	124.6	113	88.3	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

## 5.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	T <sub>A</sub> = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
V <sub>OH</sub>	I <sub>OH</sub> = -50 mA	4.5 V	4.4	4.5		4.4	V	
	I <sub>OH</sub> = -8 mA		3.94			3.8		
V <sub>OL</sub>	I <sub>OL</sub> = 50 mA	4.5 V			0.1	0.1	V	
	I <sub>OL</sub> = 8 mA				0.36	0.44		
I <sub>I</sub>	V <sub>I</sub> = 5.5 V or GND	0 V to 5.5 V			±0.1	±1	µA	
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	5.5 V			2	20	µA	
ΔI <sub>CC</sub> (1)	One input at 3.4 V, Other inputs at V <sub>CC</sub> or GND	5.5 V			1.35	1.5	mA	
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	5 V	2		10		pF	

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V<sub>CC</sub>.

## 5.5 Switching Characteristics

over recommended operating free-air temperature range, V<sub>CC</sub> = 5 V ± 0.5 V (unless otherwise noted) (see Section 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T <sub>A</sub> = 25°C			MIN	MAX	UNIT
				MIN	TYP	MAX			
t <sub>PLH</sub>	A or B	Y	C <sub>L</sub> = 15 pF		5	6.9	1	8	ns
t <sub>PHL</sub>					5	6.9	1	8	
t <sub>PLH</sub>	A or B	Y	C <sub>L</sub> = 50 pF		5.5	7.9	1	9	ns
t <sub>PHL</sub>					5.5	7.9	1	9	

## 5.6 Noise Characteristics

V<sub>CC</sub> = 5 V, C<sub>L</sub> = 50 pF, T<sub>A</sub> = 25°C (1)

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.4	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>OL</sub>		-0.4	-0.8	V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>		4.5		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2			V
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.8	V

(1) Characteristics are for surface-mount packages only.

## 5.7 Operating Characteristics

V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance (1) (2) No load, f = 1 MHz	10.5	pF

(1) C<sub>PD</sub> is used to determine the dynamic power consumption, per channel.

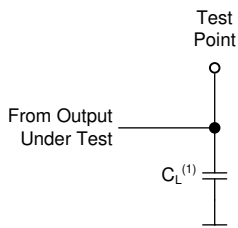
(2) P<sub>D</sub> = V<sub>CC</sub><sup>2</sup> × F<sub>I</sub> × (C<sub>PD</sub> + C<sub>L</sub>) where F<sub>I</sub> = input frequency, C<sub>L</sub> = output load capacitance, V<sub>CC</sub> = supply voltage.

## 6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \ \Omega$ .

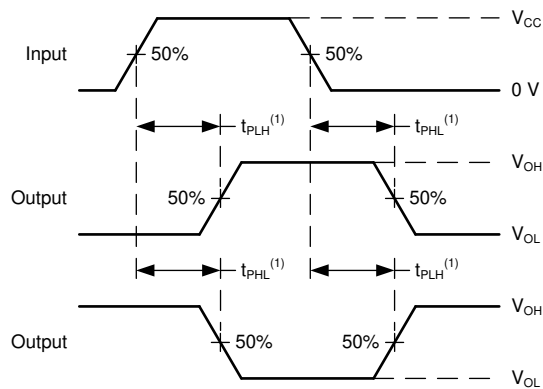
For clock inputs,  $f_{max}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



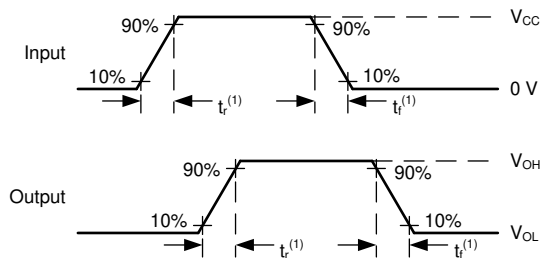
(1)  $C_L$  includes probe and test-fixture capacitance.

**Figure 6-1. Load Circuit for Push-Pull Outputs**



(1) The greater between  $t_{PLH}$  and  $t_{PHL}$  is the same as  $t_{pd}$ .

**Figure 6-2. Voltage Waveforms Propagation Delays**



(1) The greater between  $t_r$  and  $t_f$  is the same as  $t_t$ .

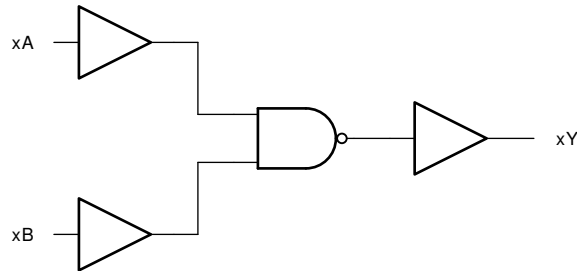
**Figure 6-3. Voltage Waveforms, Input and Output Transition Times**

## 7 Detailed Description

### 7.1 Overview

This device contains four independent 2-input NAND Gates. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

#### 7.3.2 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ( $R = V \div I$ ).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the [Implications of Slow or Floating CMOS Inputs](#) application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k $\Omega$  resistor is recommended and will typically meet all requirements.

#### 7.3.3 Clamp Diode Structure

As [Figure 7-1](#) shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

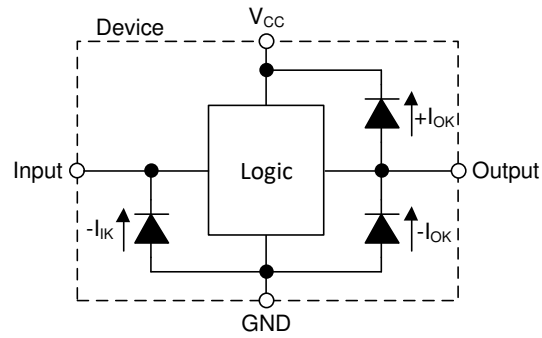
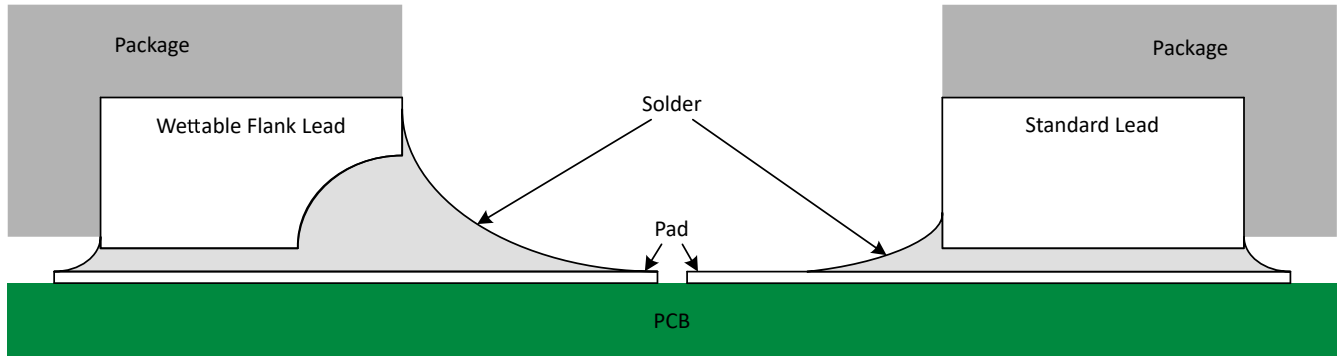


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output



### 7.3.4 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet for which packages include this feature.



**Figure 7-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering**

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in [Figure 7-2](#), a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

## 8 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

In this application, two 2-input NAND gates are used to create an active-low SR latch as shown in [Figure 8-1](#). The two additional gates can be used for a second SR latch, or the inputs can be grounded and both channels left unused.

The SN74AHCT00Q-Q1 is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the  $\bar{R}$  input which returns the Q output back to LOW.

The inputs of this active-low SR latch can often be driven by open-drain outputs which can produce slow input transition rates when they transition from LOW to Hi-Z. This makes the SN74AHCT00Q-Q1 ideal for the application because it has Schmitt-trigger inputs that do not have input transition rate requirements.

### 8.2 Typical Application

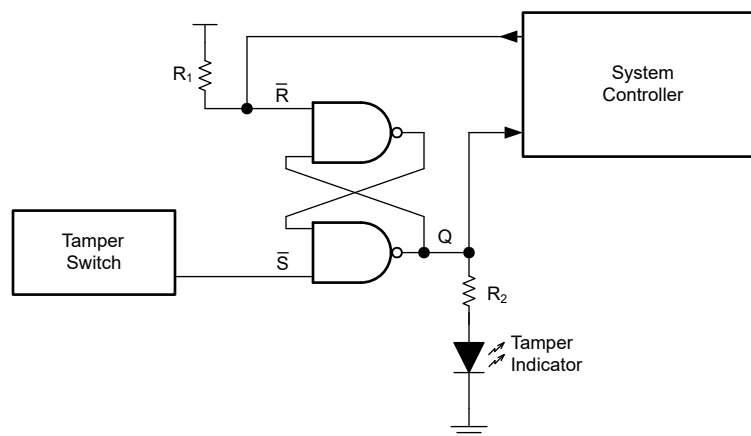


Figure 8-1. Typical Application Block Diagram

#### 8.2.1 Design Requirements

##### 8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AHCT00Q-Q1 plus the maximum static supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHCT00Q-Q1 plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into

its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74AHCT00Q-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74AHCT00Q-Q1 can drive a load with total resistance described by  $R_L \geq V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

#### **CAUTION**

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

### **8.2.1.2 Input Considerations**

Input signals must cross  $V_{IL(max)}$  to be considered a logic LOW, and  $V_{IH(min)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHCT00Q-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74AHCT00Q-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

### **8.2.1.3 Output Considerations**

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

## 8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is  $\leq 50$  pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHCT00Q-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in  $M\Omega$ ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

## 8.2.3 Application Curves

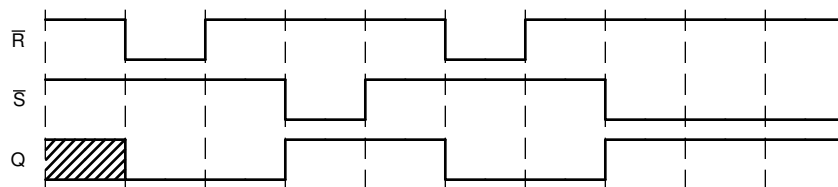


Figure 8-2. Application Timing Diagram

## 8.3 Power Supply Recommendations

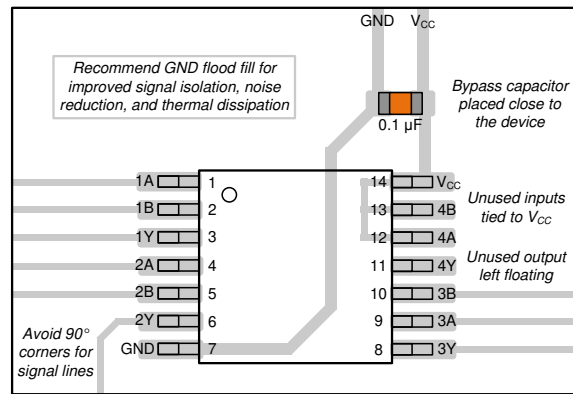
The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Layout Example*.

## 8.4 Layout

### 8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

### 8.4.2 Layout Example



**Figure 8-3. Example Layout for the SN74AHCT00Q-Q1**

## 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

### 9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (May 2023) to Revision D (February 2024)	Page
• Updated R $\theta$ JA value: D = 86 to 124.6, all values in °C/W .....	4

Changes from Revision B (May 1998) to Revision C (May 2023)	Page
• Updated the <i>Features</i> section .....	1
• Added the <i>Applications</i> section.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Added the <i>BQA</i> package information throughout the document.....	1
• Added the <i>Pin Configuration and Functions</i> section.....	3
• Updated the <i>Parameter Measurement Information</i> section.....	6
• Added the <i>Detailed Description</i> sections.....	7

- 
- Added the *Application and Implementation* sections..... 10
- 

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHCT00QDRG4Q1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT00Q	<a href="#">Samples</a>
SN74AHCT00QDRQ1	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT00Q	<a href="#">Samples</a>
SN74AHCT00QPWRG4Q1	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HB00Q	<a href="#">Samples</a>
SN74AHCT00QPWRQ1	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HB00Q	<a href="#">Samples</a>
SN74AHCT00QWBQARQ1	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHT00Q	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHCT00QPWRG4Q1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHCT00QWBQARQ1	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHCT00QPWRG4Q1	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74AHCT00QWBQARQ1	WQFN	BQA	14	3000	210.0	185.0	35.0

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  -  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AB.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4040064-3/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

## GENERIC PACKAGE VIEW

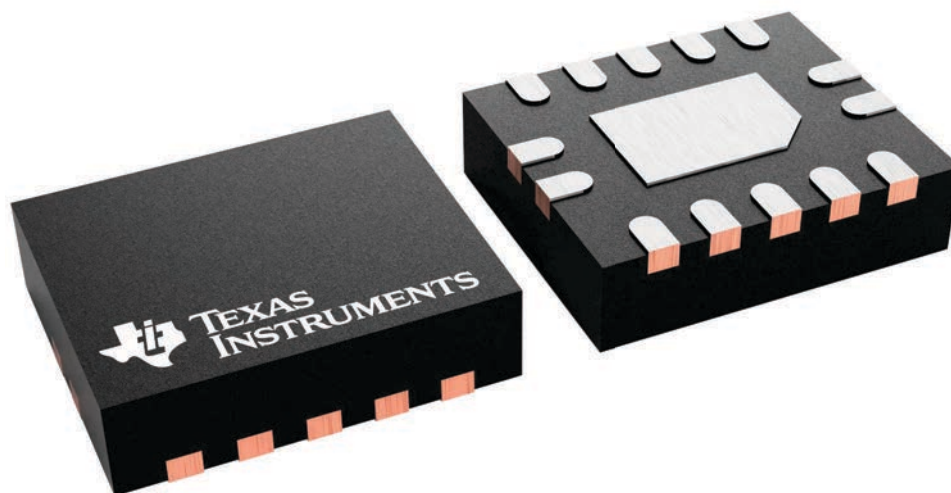
**BQA 14**

**WQFN - 0.8 mm max height**

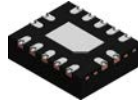
2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



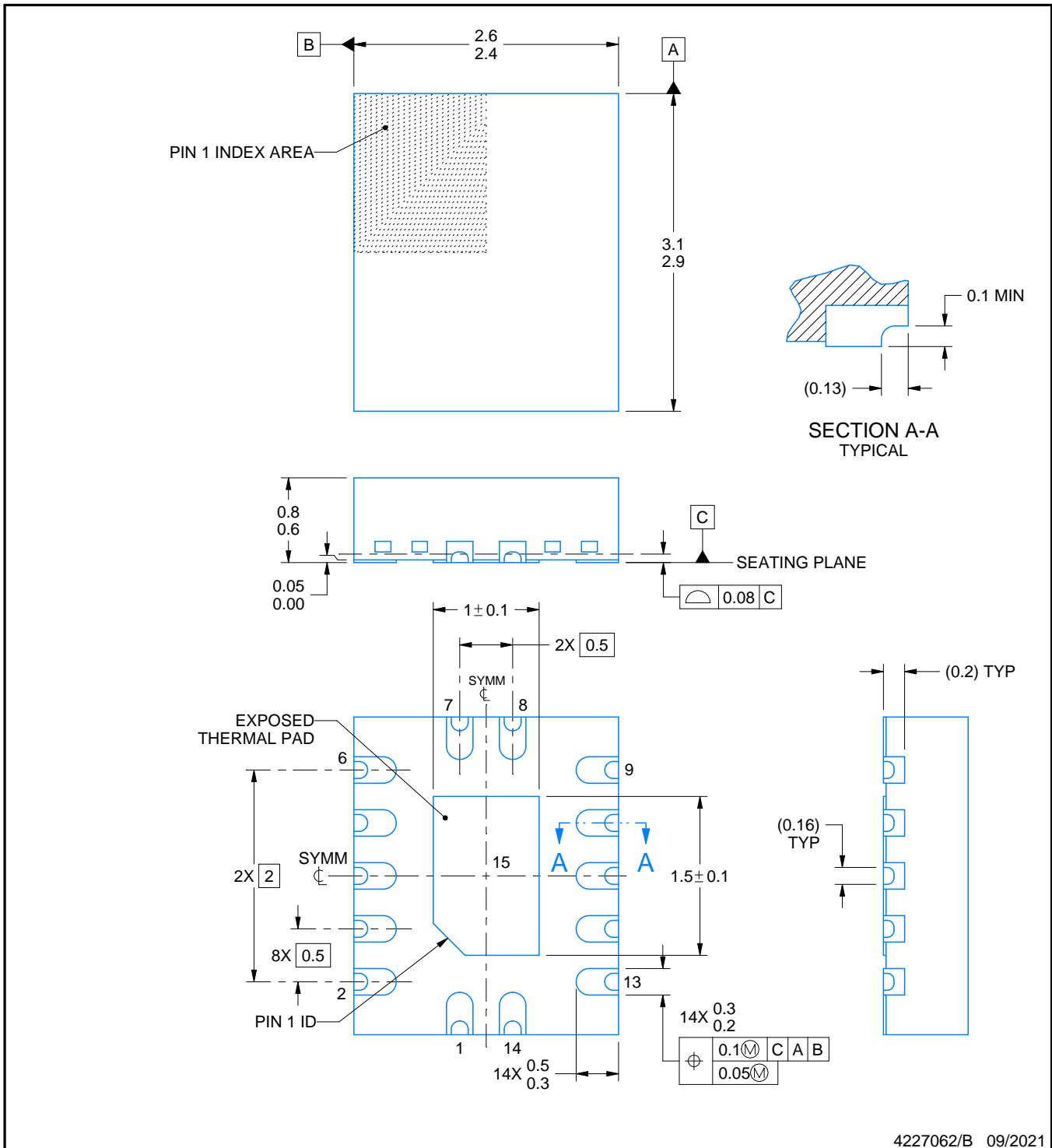
# BQA0014B



# PACKAGE OUTLINE

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



**NOTES:**

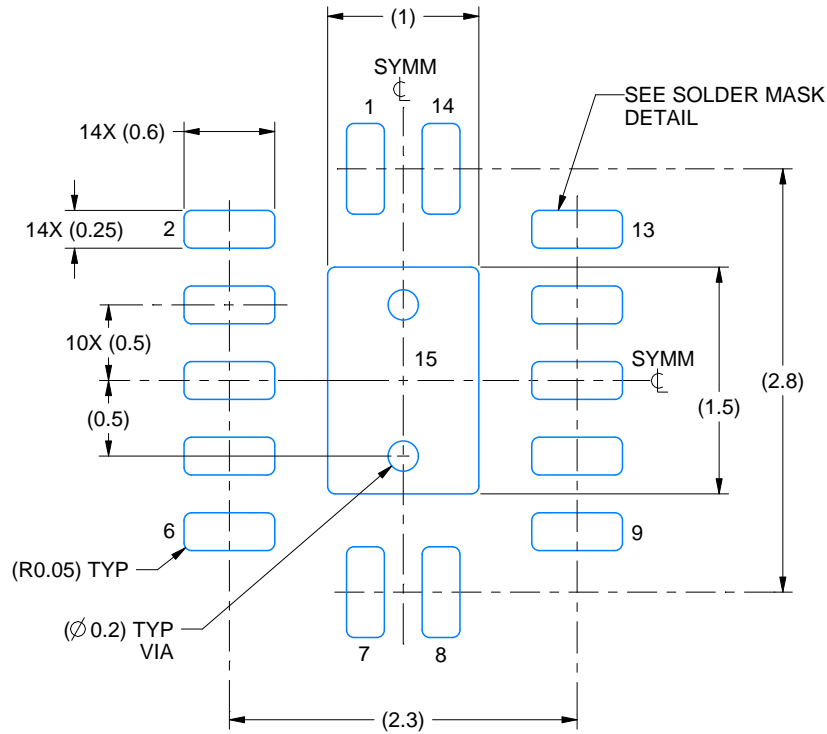
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

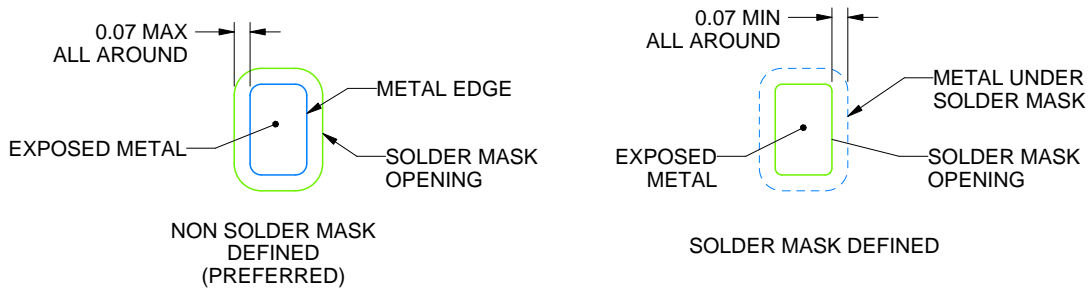
**BQA0014B**

**WQFN - 0.8 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 20X



SOLDER MASK DETAILS

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NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



# EXAMPLE STENCIL DESIGN

BQA0014B

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 MM THICK STENCIL  
SCALE: 20X

EXPOSED PAD 15  
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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